DRAF114Y

Silicon PNP epitaxial planar type

For digital circuits Complementary to DRCF114Y DRA3114Y in ML3 type package

Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, mount area reduction
- Eco-friendly Halogen-free package

Packaging

DRAF114Y0L Embossed type (Thermo-compression sealing): 10000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation *	P _T	100	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Note) *: Copper plate at the collector is 5.0 mm^2 on substrate at $10 \text{ mm} \times 12 \text{ mm} \times 0.8 \text{ mm}$.

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$							
Parameter	Symbol	Conditions	Min	Тур	Max		
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50				
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50				
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$			-0.1		
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -50$ V, $I_{\rm B} = 0$			-0.5		
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			-0.2		
Forward current transfer ratio	h _{FE}	$V_{\rm CE} = -10$ V, $I_{\rm C} = -5$ mA	80				
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25		
Input voltage (ON)	V _{I(on)}	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-1.7				
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			-0.5		

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

 R_1

 R_1 / R_2

Package

- Code
- ML3-N4-B
 - Package dimension clicks here. $\!\rightarrow$

• Pin Name

- 1: Base
- 2: Emitter
- 3: Collector

Marking Symbol: LC

Internal Connection

-30%

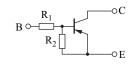
0.17

10

0.21

+30%

0.25



Resistance value	R ₁	10	kΩ
	R ₂	47	kΩ

Unit V µA mA mA V V V

kΩ

Input resistance

Resistance ratio

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